



STW33N60DM2 Information



For Reference Only

Part Number STW33N60DM2

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 24A

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STW33N60DM2 Specifications

Manufacturer Part Number STW33N60DM2 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series MDmesh? DM2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1870pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1870pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs130 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Package	TO-247-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1870pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs130 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Series	MDmesh? DM2
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Current - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1870pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs130 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1870pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs130 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	24A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1870pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs130 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	43nC @ 10V
FET Feature - 190W (Tc) Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	1870pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs 130 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Power Dissipation (Max)	190W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	130 mOhm @ 12A, 10V
Supplier Device Package TO-247 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247
Report errors?	Package / Case	TO-247-3
		Report errors?

STW33N60DM2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STW33N60DM2 Payment Methods



















STW33N60DM2 Shipping Methods













If you have any question about STW33N60DM2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com